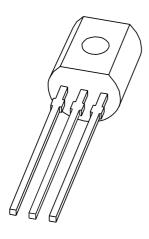
DISCRETE SEMICONDUCTORS

DATA SHEET



PSS9015B PNP general purpose transistor

Product specification

2002 Sep 20





PNP general purpose transistor

PSS9015B

FEATURES

• Low collector capacitance.

APPLICATIONS

- General purpose switching and amplification
- Low frequency, low noise amplifier.

DESCRIPTION

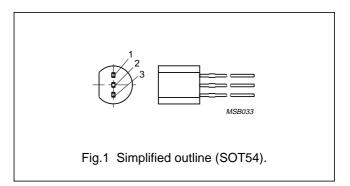
PNP transistor in a SOT54 plastic package. NPN complement: PSS9014.

MARKING

TYPE NUMBER	MARKING CODE
PSS9015B	S9015B

PINNING

PIN	DESCRIPTION
1	collector
2	base
3	emitter



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	-50	V
V_{CEO}	collector-emitter voltage	open base	_	-45	٧
V _{EBO}	emitter-base voltage	open collector	_	- 5	٧
I _C	collector current (DC)		_	-100	mA
I _{CM}	peak collector current		_	-200	mA
I _{BM}	peak base current		_	-200	mA
P _{tot}	total power dissipation	up to T _{amb} = 25 °C; note 1	_	500	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

1. Device mounted on a printed-circuit board; single sided copper; tinplated; standard footprint.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to	in free air; note 1	240	K/W
	ambient			

Note

1. Device mounted on a printed-circuit board; single sided copper; tinplated; standard footprint.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	$V_{CB} = -30 \text{ V; } I_E = 0$	_	_	-50	nA
		$V_{CB} = -30 \text{ V}; I_E = 0;$ $T_{amb} = 150 \text{ °C}$	_	_	-5	μΑ
I _{CEO}	collector-emitter cut-off current	$V_{CE} = -30 \text{ V}; I_B = 0$	_	_	-100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0$	_	_	-100	nA
h _{FE}	DC current gain	$I_C = -1 \text{ mA}; V_{CE} = -5 \text{ V}$	100	200	300	
V _{CEsat}	saturation voltage	$I_C = -100 \text{ mA}; I_B = -5 \text{ mA}; \text{ note } 1$	_	_	-700	mV
V _{BEsat}	saturation voltage	$I_C = -100 \text{ mA}; I_B = -5 \text{ mA}; \text{ note } 1$	_	_	-1000	mV
V _{BEon}	base-emitter turn-on voltage	$I_C = -2 \text{ mA}; V_{CE} = -5 \text{ V}$	-600	_	-750	mV
f⊤	transition frequency	I _C = -10 mA; V _{CE} = -10 V; f = 100 MHz	100	_	-	MHz
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = I_e = 0;$ f = 1 MHz	_	_	7	pF
F	noise figure	$V_{CE} = -5 \text{ V; } I_{C} = -0.2 \text{ mA;}$ $R_{S} = 1 \text{ k}\Omega; f = 1 \text{ kHz; } B = 200 \text{ Hz}$	_	_	10	dB

Note

1. Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02.$

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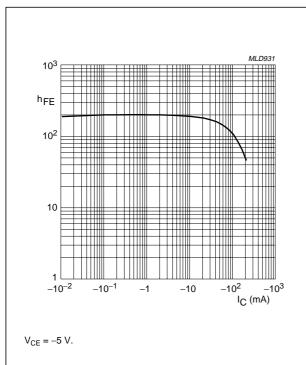
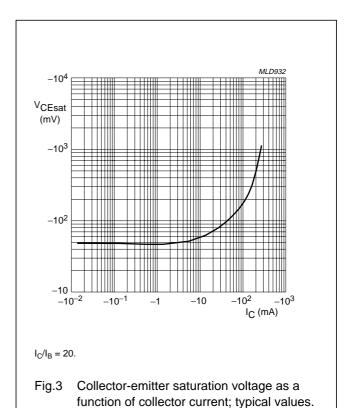
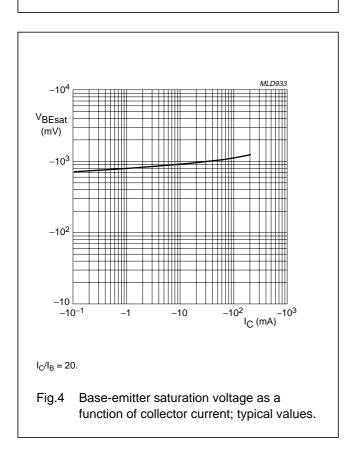
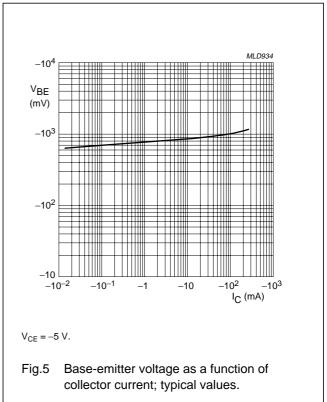


Fig.2 DC current gain as a function of collector current; typical values.







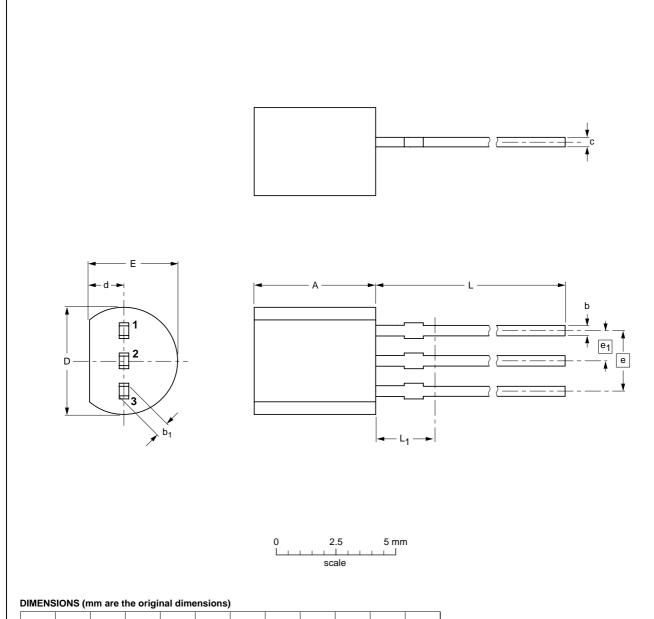
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PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



UNIT	Α	b	b ₁	U	D	d	E	е	e ₁	L	L ₁ ⁽¹⁾
mm	5.2 5.0	0.48 0.40	0.66 0.56	0.45 0.40	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE		REFERENCES			FERENCES EUROPEAN ISSUE DATE			
VERSION	IEC	JEDEC	EIAJ		PROJECTION ISSUE			
SOT54		TO-92	SC-43			97-02-28		

PNP general purpose transistor

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DATA SHEET STATUS

DATA SHEET STATUS(1)	PRODUCT STATUS ⁽²⁾	DEFINITIONS
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PNP general purpose transistor

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Contact information

For additional information please visit http://www.semiconductors.philips.com. Fax: +31 40 27 24825 For sales offices addresses send e-mail to: sales.addresses@www.semiconductors.philips.com.

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Printed in The Netherlands

613514/01/pp8

Date of release: 2002 Sep 20

Document order number: 9397 750 10188

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